

## General Description

The WSP4800 is the highest performance trench N-ch MOSFET with extreme high cell density, which provide excellent RDSON and gate chargens for most of the synchronous buck converter applications .

The WSP4800 meet the RoHS and Green Product requirement, 100% EAS guaranteed with full function reliability approved.

## Features

- Advanced high cell density Trench technology
- Super Low Gate Charge
- Excellent CdV/dt effect decline
- 100% EAS Guaranteed
- Green Device Available

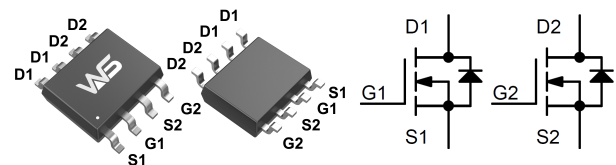
## Product Summary

BVDSS	RDSON	ID
40V	32mΩ	6.0A

## Applicatio

- Power Management in Note book.
- Battery Powered System.
- Industrial DC/DC Conversion Circuits

## SOP-8 Pin Configuration



## Absolute Maximum Ratings

Symbol	Parameter	Rating	Units
$V_{DS}$	Drain-Source Voltage	40	V
$V_{GS}$	Gate-Source Voltage	$\pm 20$	V
$I_D@T_C=25^\circ C$	Continuous Drain Current, $V_{GS} @ 10V$	6.0	A
$I_D@T_C=70^\circ C$	Continuous Drain Current, $V_{GS} @ 10V$	5.4	A
$I_{DM}$	Pulsed Drain Current <sup>a</sup>	28	A
$P_D@T_A=25^\circ C$	Total Power Dissipation $T_A=25^\circ C$	1.5	A
$P_D@T_A=70^\circ C$	Total Power Dissipation $T_A=70^\circ C$	1.28	W
$T_{STG}$	Storage Temperature Range	-55 to 150	$^\circ C$
$T_J$	Operating Junction Temperature Range	-55 to 150	$^\circ C$

## Thermal Data

Symbol	Parameter	Typ.	Max.	Unit
$R_{\theta JA}$	Thermal Resistance Junction-ambient <sup>b</sup>	---	110	$^\circ C/W$
$R_{\theta JC}$	Thermal Resistance Junction-Case	---	62.5	$^\circ C/W$

Note a : Pulse width limited by max. junction temperature.

Note b : Surface Mounted on 1in<sup>2</sup> pad area, t =999sec.

Note c : UIS tested and pulse width limited by maximum junction temperature 150 $^\circ C$  (initial temperature  $T_J=25^\circ C$ ).

**Electrical Characteristics (T<sub>J</sub>=25 °C, unless otherwise noted)**

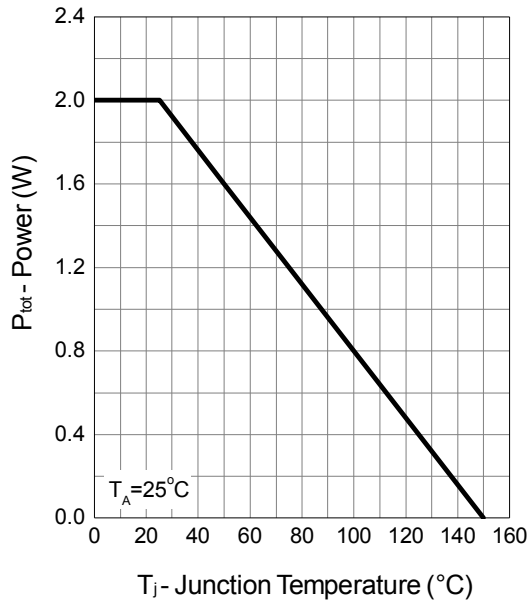
Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV <sub>DSS</sub>	Drain-Source Breakdown Voltage	V <sub>GS</sub> =0V, I <sub>D</sub> =250μA	40	---	---	V
R <sub>DS(ON)</sub> <sup>c</sup>	Static Drain-Source On-Resistance <sup>2</sup>	V <sub>GS</sub> =10V, I <sub>D</sub> =6.0A	---	32	35	mΩ
		V <sub>GS</sub> =4.5V, I <sub>D</sub> =5.0A	---	36	40	
V <sub>GS(th)</sub>	Gate Threshold Voltage	V <sub>GS</sub> =V <sub>DS</sub> , I <sub>D</sub> =250μA	1.0	1.6	2.5	V
I <sub>DSS</sub>	Drain-Source Leakage Current	V <sub>DS</sub> =24V, V <sub>GS</sub> =0V, T <sub>J</sub> =25°C	---	---	1	μA
		V <sub>DS</sub> =24V, V <sub>GS</sub> =0V, T <sub>J</sub> =55°C	---	---	30	
I <sub>GSS</sub>	Gate-Source Leakage Current	V <sub>GS</sub> =±20V, V <sub>DS</sub> =0V	---	---	±100	nA
Q <sub>g</sub> <sup>d</sup>	Total Gate Charge (4.5V)	V <sub>DS</sub> =20V, V <sub>GS</sub> =4.5V, I <sub>D</sub> =6A	---	7.5	---	nC
Q <sub>gs</sub>	Gate-Source Charge		---	3.24	---	
Q <sub>gd</sub>	Gate-Drain Charge		---	2.75	---	
T <sub>d(on)</sub>	Turn-On Delay Time	V <sub>DD</sub> =20V, V <sub>GEN</sub> =10V, R <sub>G</sub> =6Ω , I <sub>D</sub> =1A, R <sub>L</sub> =20Ω.	---	7.8	---	ns
T <sub>r</sub>	Rise Time		---	6.9	---	
T <sub>d(off)</sub>	Turn-Off Delay Time		---	22.4	---	
T <sub>f</sub>	Fall Time		---	4.8	---	
C <sub>iss</sub>	Input Capacitance	V <sub>DS</sub> =20V, V <sub>GS</sub> =0V, f=1MHz	---	815	---	pF
C <sub>oss</sub>	Output Capacitance		---	95	---	
C <sub>rss</sub>	Reverse Transfer Capacitance		---	60	---	

Note c : Pulse test ; pulse width≤300μs, duty cycle≤2%.

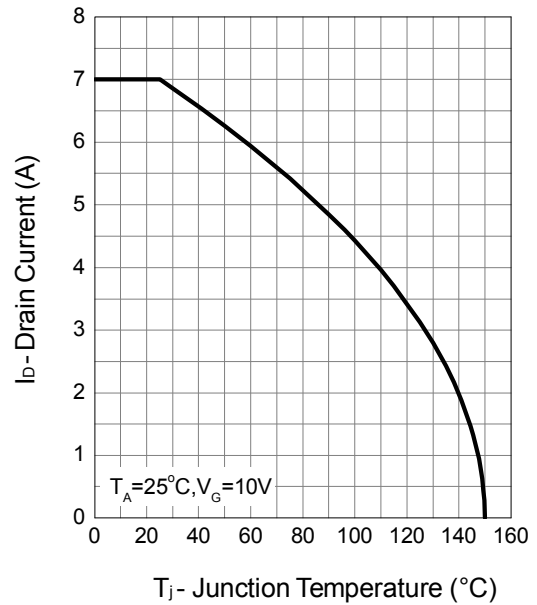
Note d : Guaranteed by design, not subject to production testing.

Typical Characteristics

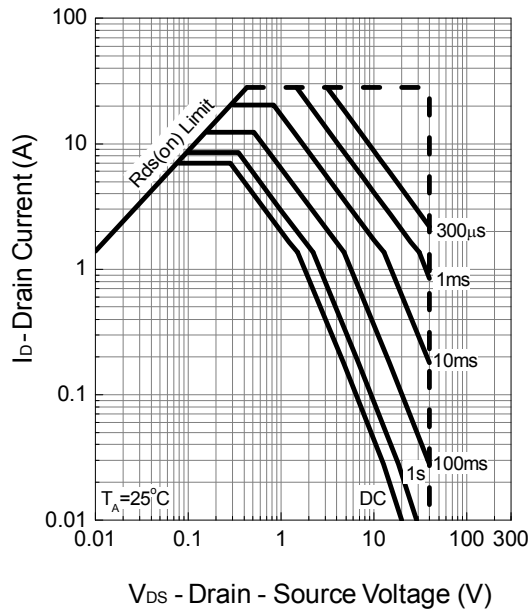
Power Dissipation



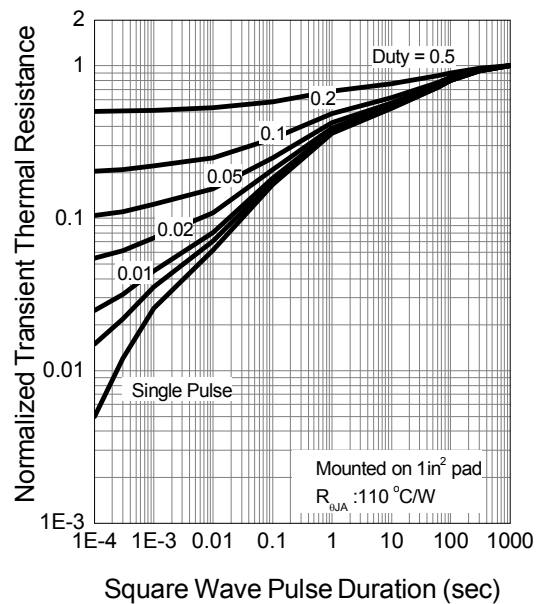
Drain Current



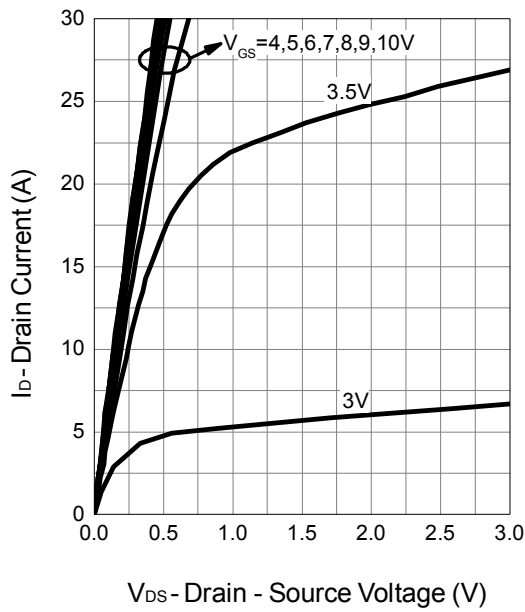
Safe Operation Area



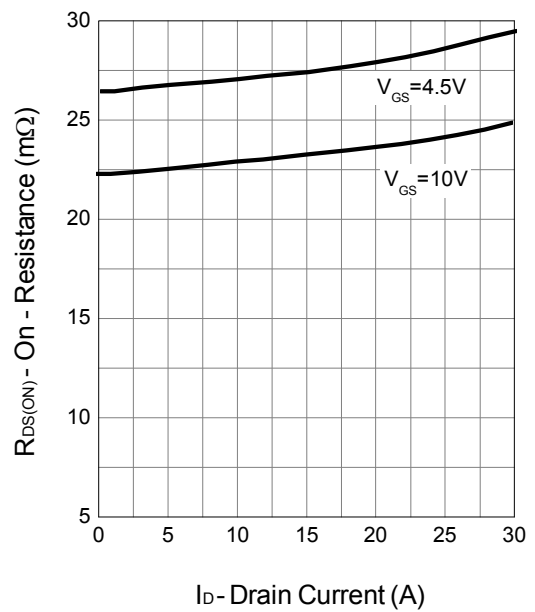
Thermal Transient Impedance



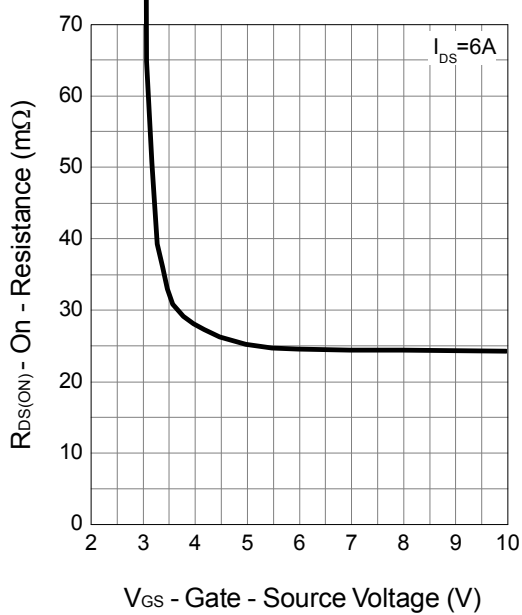
**Output Characteristics**



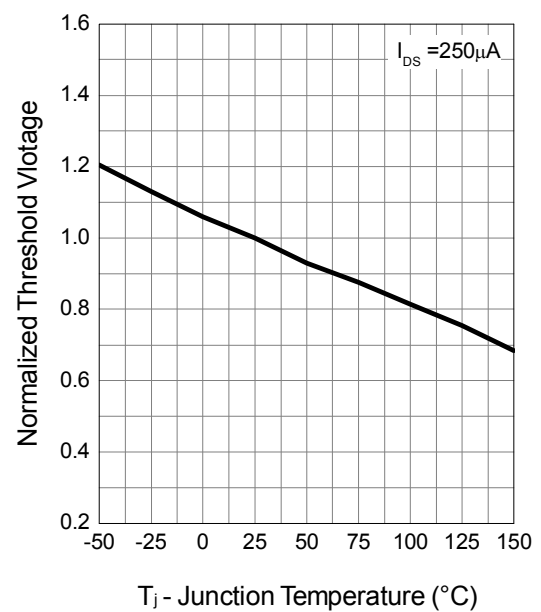
**Drain-Source On Resistance**



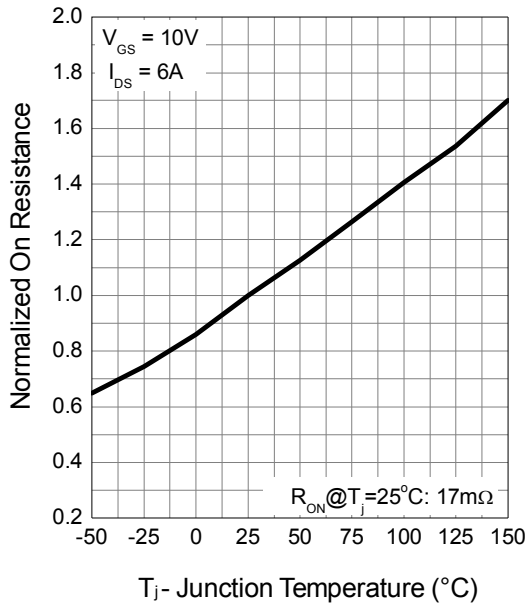
**Gate-Source On Resistance**



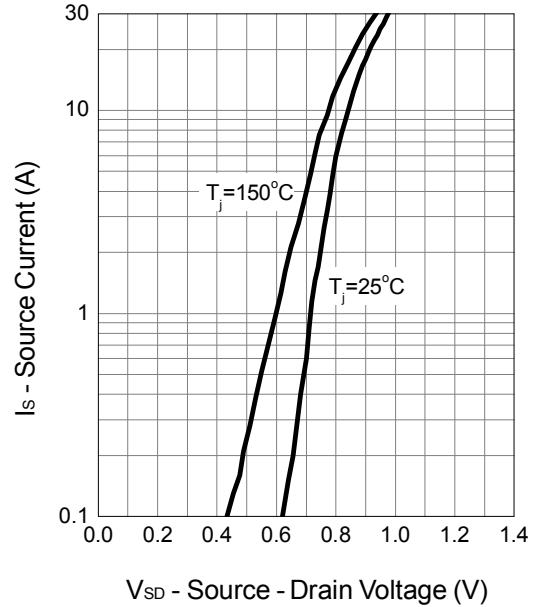
**Gate Threshold Voltage**



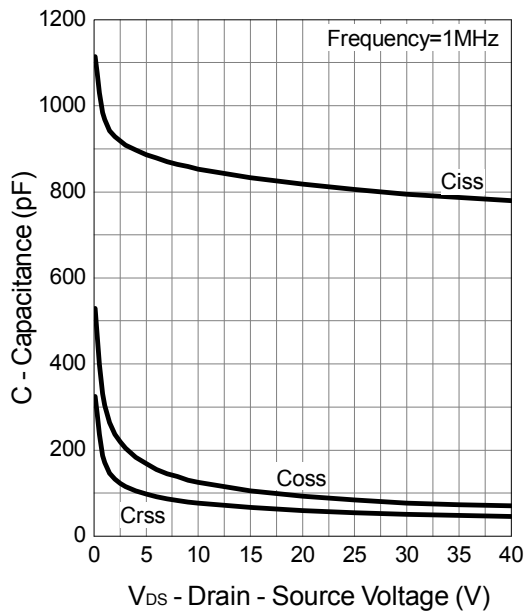
**Drain-Source On Resistance**



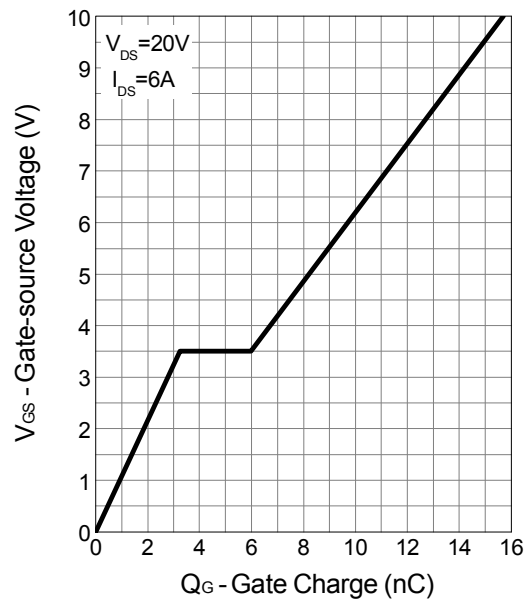
**Source-Drain Diode Forward**



**Capacitance**



**Gate Charge**





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